Investor Presentation

March 2018

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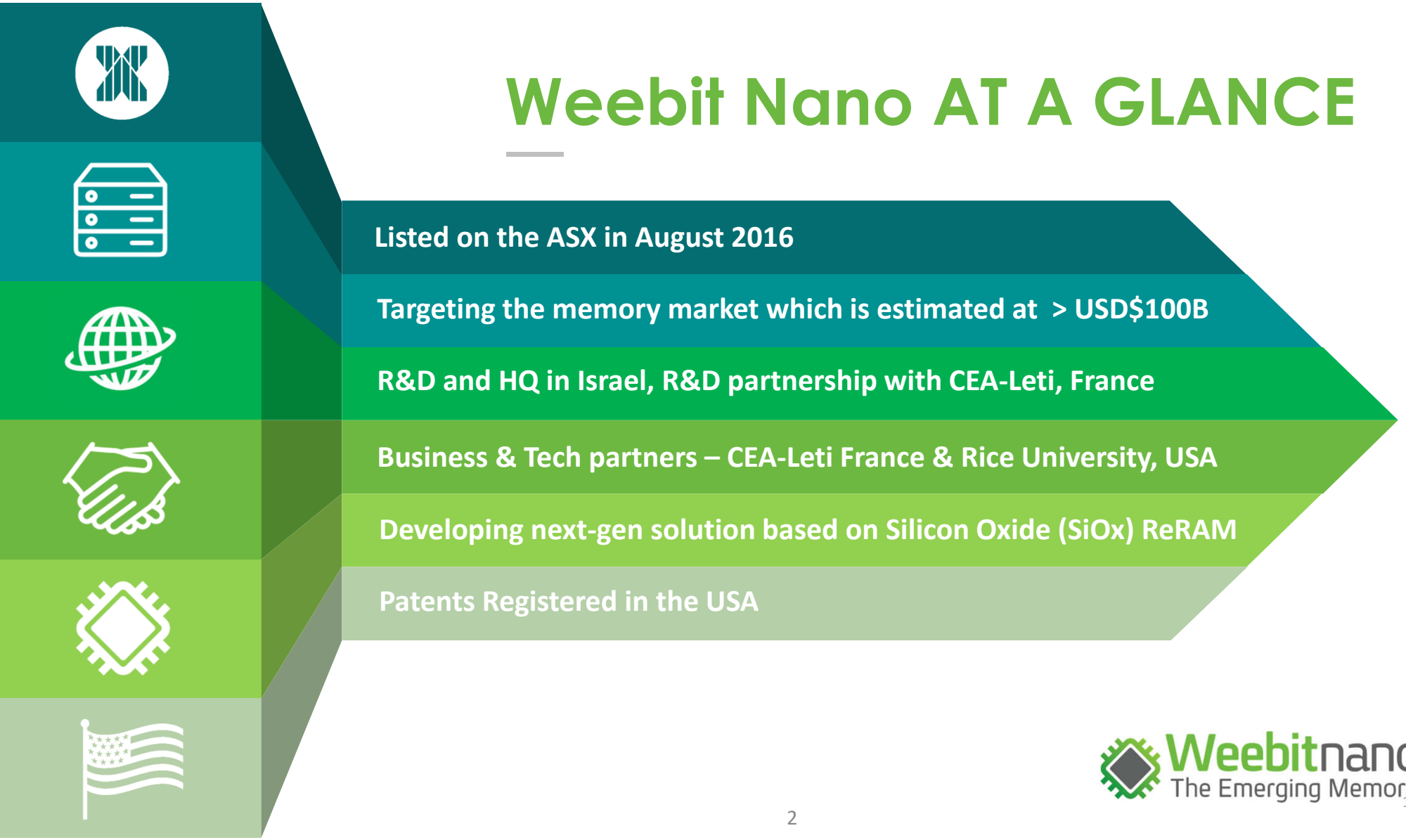
Weebit Nano AT A GLANCE



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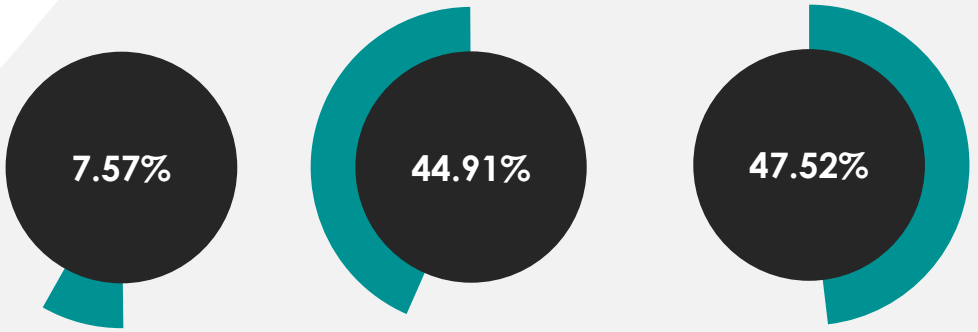
SHARE INFORMATION

CAPITAL STRUCTURE

01	ASX Code: WBT
02	Share price: 5.0c[1]
03	Shares on issue: 1443m[1]
04	Options: 150m[1,2]
05	Market cap: A$72m[1]
06	Cash: $3.4m[3]

1. As of 16 March 2018
2. Including performance shares
3. As of 31 December 2017

SHAREHOLDING BREAKDOWN



BOARD & MANAGEMENT

TOP 20
Excluding Board & Management

OTHER

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INTRODUCING
DR. YOAV NISSAN-COHEN

- PhD in Applied Physics focused on SiOx memories
  - Guided by Prof. Dov Frohman, the inventor of the first Non-Volatile memory
  - Consulted to Intel corporation on Non-Volatile Memories
- Researcher in GE R&D center in NY, focused on semiconductor devices
- Extensive experience as a CEO of public and private companies
  - CEO of Tower semiconductors (NASDAQ:TSEM) for 9 years, leading the spinout from National Semiconductor
  - Chairman & CEO of Amimon, a semiconductor startup, for 7 years
  - Chairman & CEO of Zullavision, a technology startup, for 4 years
- 2 years Partner in $1B Pitango Venture Capital fund
- Board member of Saifun Semiconductor, pioneering NROM Flash

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INTRODUCING FRED BART

- Transformed his family business to a $200M business
- Vast business experience in many different domains
  - Including multiple ASX listed companies
- Chairman and major shareholder of Electro Optics Systems (ASX:EOS)
  - Market capitalisation of $263M[1]
- Chairman of Audio Pixels (ASX:AKP) since 2010
  - Market capitalisation of $454M[1]
- Acquired and turned around multiple companies
- Owns multiple companies worldwide

1) As of 19 March, 2018

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FIRST CLASS LEADERSHIP TEAM

EXECUTIVE DIRECTOR

Yoav Nissan-Cohen

PhD. in Applied Physics, focus on SiOx memories

CEO of Tower Semiconductor for 9 years

Board member, Saifun Semiconductor (NROM Flash)

CHAIRMAN

David Perlmutter

Ex-Intel EVP
IEEE Fellow

Led Intel into the Data Center

Brought to Market: Centrino™ mobile technology

CEO

Coby Hanoch

Extensive management and sales experience

37 years in the semiconductor domain

Heavily involved in Verisity and Jasper acquisitions

CTO

Amir Regev

Two decades in Semiconductor engineering

45nm NOR Flash Technology Development at Micron

Was part of Automotive division at Intel

CFO

Alla Felder

20 Years CPA experience

Senior Manager at PWC Israel

Active Board member of multiple companies in TASE and NASDAQ

HIGHLY SKILLED NON-EXEC/ADVISORY TEAM

DIRECTOR

Fred Bart

Chairman and major shareholder of Electro Optics Systems (EOS)

Chairman of Audio Pixels (AKP)

Owns a wide variety of companies worldwide

DIRECTOR

Ashley Krongold

15 years in Investment Banking

Founding member of Investec Bank Australia

Founding General Partner, OurCrowd

DIRECTOR

Yossi Keret

Extensive management and financial experience

Led the financial teams at a number of publicly traded international companies

Strong experience in equity raisings for public companies

INVENTOR

Prof. James Tour

Scientist of the Year 2013 R&D magazine

Inducted to the National Academy of inventors

Feynman prize in Nano science

WEEBIT ReRAM TECHNOLOGY

Next generation memory technology

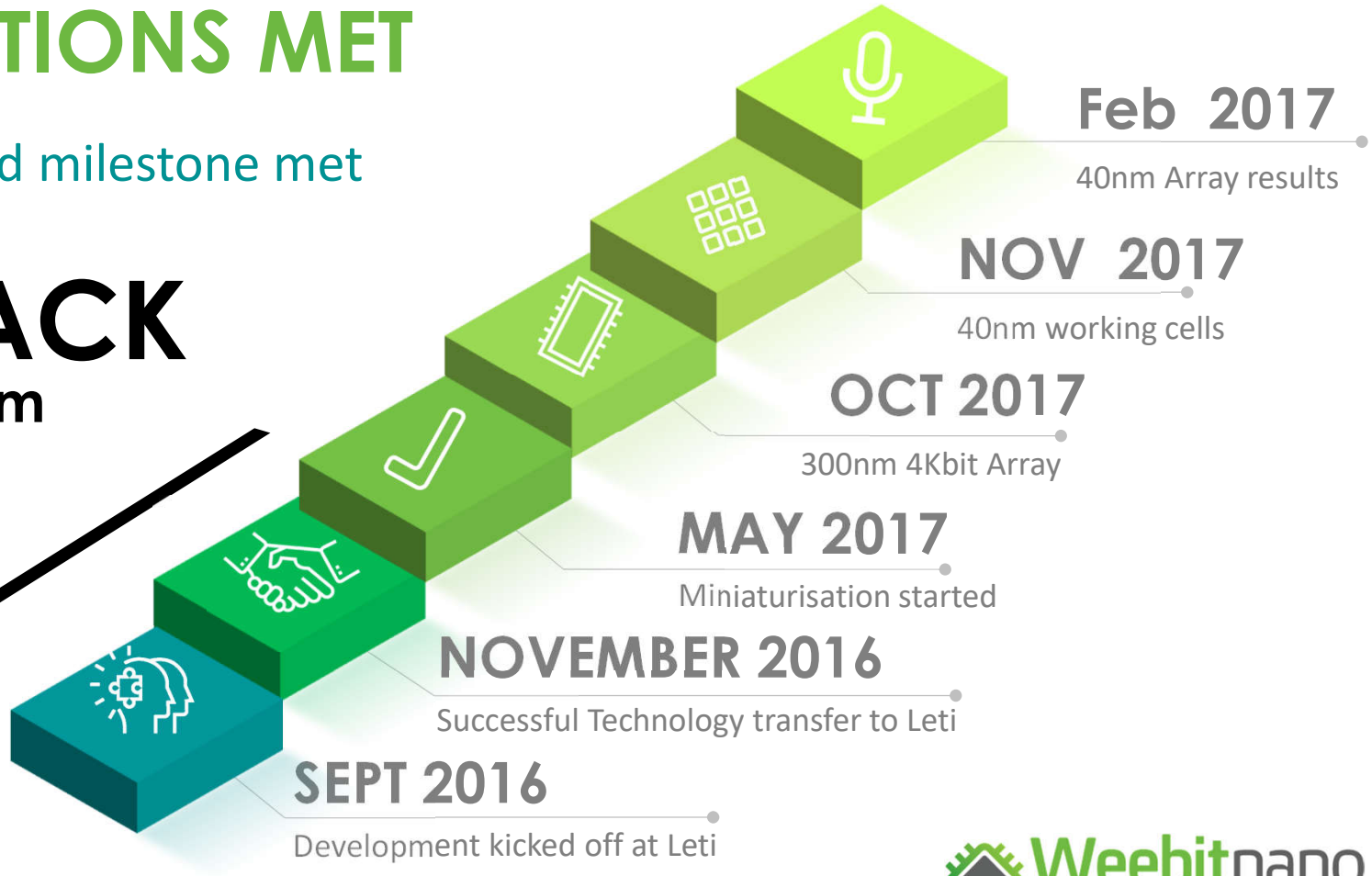
- **Faster and more efficient than flash memory**
- **On track to achieve 40nm 1Mb array by mid-2018 – comparable with current embedded memory technology**
- **Key differentiator: WBT uses silicon oxide – the most commonly used material in the semiconductor industry**
- **Silicon oxide enables lower cost and shorter time to market**

EXPECTATIONS MET

Every committed milestone met

ON TRACK

to reach 40nm Mbit array by mid-2018



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ALLIANCE WITH CEA - LETI

A real partnership, with ideal mix of expertise, innovation and flexibility

FROM PROTOTYPES TO PRODUCTION
Proven international track record in moving from R&D to production

MEMORY EXPERTISE
Over 10 years of experience in memory technology development

NANOTECHNOLOGY SPECIALIST
State of the art industrial tools

MANUFACTURING ALLIANCES
Over 330 industrial partners

INNOVATION HUB
60+ start-ups in semiconductor, architectures or software

COLLABORATION
Working on 40nm SiOx development since September 2016

CUSTOMERS
Intel, ST Microelectronics, Global foundries

leti
cea tech

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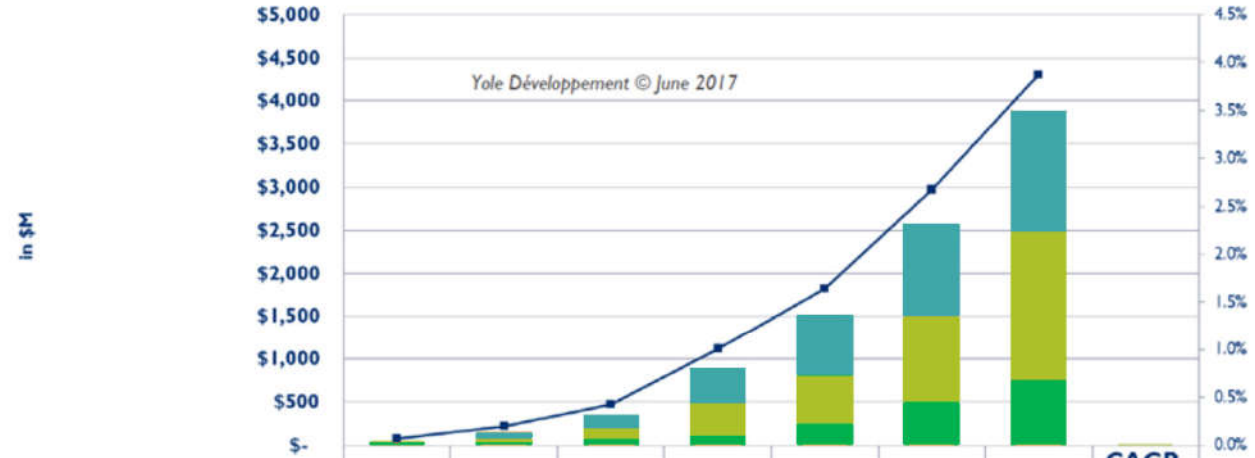
ReRAM: FORECAST FOR EXPONENTIAL GROWTH IN MARKET VALUE

Emerging Non-Volatile Memory Forecast by Technology (in $M)



	2016	2017	2018	2019	2020	2021	2022	CAGR 2016-2022
TOTAL in $M	$51	$161	$361	$898	$1,523	$2,581	$3,891	106%
PCM	$-	$90	$162	$413	$721	$1,077	$1,409	0%
RRAM	$16	$28	$132	$365	$561	$1,010	$1,727	119%
MRAM/STT MRAM	$35	$43	$66	$120	$242	$493	$754	67%
% emerging NVM vs total memory market	0.1%	0.2%	0.4%	1.0%	1.6%	2.7%	3.9%	

- Emerging memory technologies forecast for significant growth
- ReRAM technology expected to be the fastest growing emerging memory technology with a CAGR of 119%
- ReRAM forecast growth due to competitive cost/performance in both storage class memory and mass storage applications

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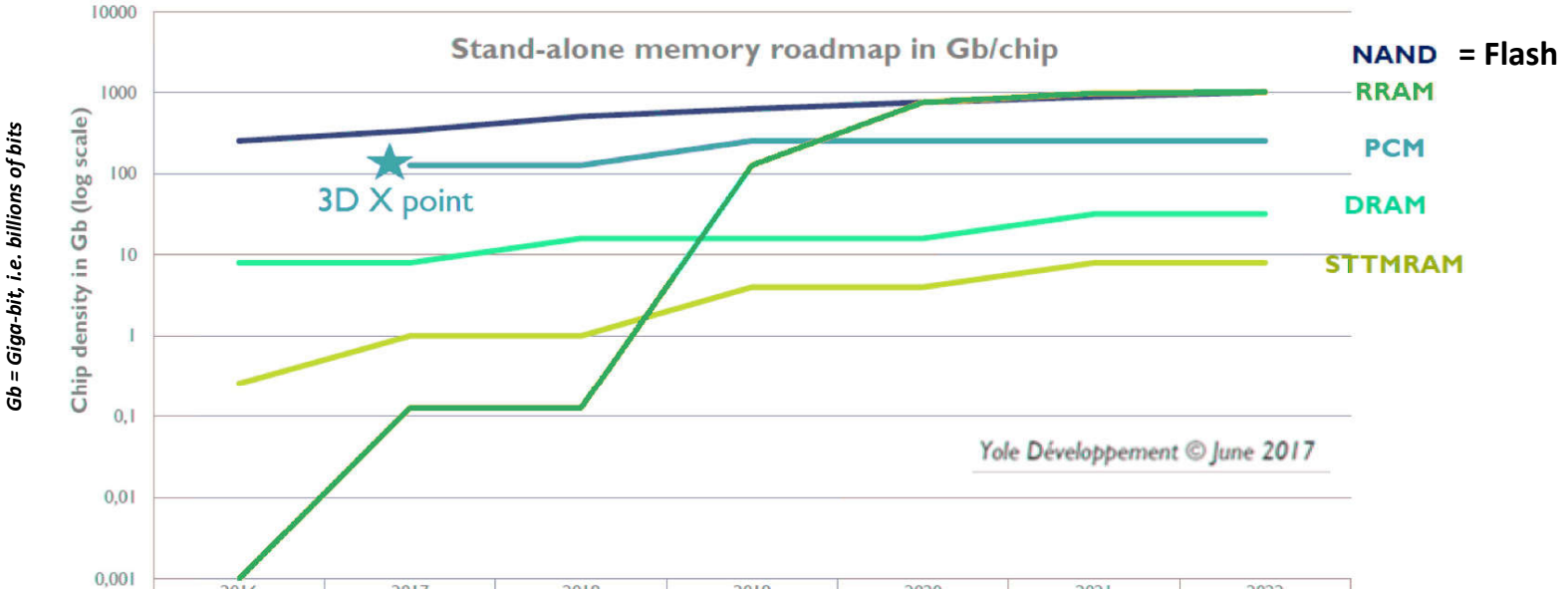
ReRAM DENSITY WILL MATCH FLASH

Highest capacity memory chips best address Storage Class Memory



Gb = Giga-bit, i.e. billions of bits

	2016	2017	2018	2019	2020	2021	2022
NAND	256	342	512	640	768	896	1024
DRAM	8	8	16	16	16	32	32
MRAM	0,256	1	1	4	4	8	8
PCM		128	128	256	256	256	256
RRAM	0,001	0,127	0,127	128	768	1000	1024

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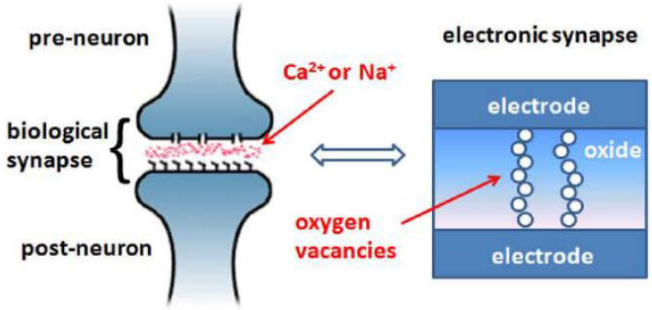
NEUROMORPHIC COMPUTATION

ReRAM well positioned for significant growth in Artificial Intelligence

- ReRAM's operation mimics the biological computation at the synaptic level
  - Physical similarities lead to functional similarities
  - Combines memory and processing units using synapse and neuron like cells
  - **ReRAM for AI is significantly more energy efficient than today's data centres, and significantly smaller**
- ReRAM is therefore very well placed to capitalise on the emergence of AI capabilities



Ions migration leads to resistivity modulation

ReRAM technology enables brain-inspired AI systems

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ReRAM COMPETITIVE LANDSCAPE

Speed to market is a significant competitive advantage

	Weebitnano	4DS	Crossbar	adesto TECHNOLOGIES
Materials *	Silicon Oxide	Pr, Ca, Mn	Silver	Tellurium
Memory Capacity	40nm 4Kb achieved Mb Array by mid-2018	Start work on Mb Array	8Mb Array	512Kb
Retention	10Y > room temp	No data	10Y @ 85 °C	40Y @ 125 °C
Endurance	10^5 **	10^3	10^6	10^5
Dimension	40nm	40nm	40nm	130nm
Development time	<2 years	7 years	7 years	>10 years

*** Pr, Ce** – rare earth **Mn Ag, Ca** – not fab friendly

*** moving to 10^6*

Based on public information

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2018 PLANS

TECHNICAL

- Develop a 40nm Mbit array by mid-2018
  - ✓ Addresses most needs of the embedded memory market
- Improved endurance and retention to meet industry standards by end 2018
- Define a plan and be on the path to develop 28nm technology
  - ✓ Will open up new potential uses for WBT's technology

BUSINESS

- Sign first cooperation agreement with a key industry player
- Explore collaborations with other technologies that can complement WBT's technology

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